

AMENDMENTS TO THE CLAIMS

1. (Previously Presented) A method comprising:
introducing an etch stop layer on a substrate;
introducing a base layer on the etch stop layer;
introducing a dielectric cap layer on the base layer between an interconnection line and a contact point on the substrate, the dielectric cap layer comprising alternating different material layers, wherein each respective layer of the alternating different material layers is selectively etchable with respect to the etch stop layer and the number of occurrences of each different material layer is greater than one;
introducing a photoimageable material on the dielectric cap layer; and
patterning an interconnection to the contact point, wherein the dielectric cap layer is configured to suppress substrate reflections during patterning.
2. (Original) The method of claim 1, wherein patterning an interconnection to the contact point comprises patterning an interconnection directly to a device on the substrate.
3. (Canceled)
4. (Previously Presented) The method of claim 1, wherein the introducing the dielectric cap layer comprises introducing silicon dioxide as an ultimate layer.
5. (Previously Presented) The method of claim 4, wherein introducing alternating different material layers comprises alternating silicon dioxide layers with at least one other material layers.
6. (Original) The method of claim 5, wherein the number of alternating silicon dioxide layers comprises at least six.

7. (Previously Presented) The method of claim 1, wherein the dielectric cap layer comprises a first dielectric layer, the method further comprising introducing a second dielectric layer between the first dielectric layer and the etch stop layer.

8-17. (Canceled)

18. (Previously Presented) The method of claim 1, further comprising introducing a photoimageable material layer, wherein the dielectric cap layer comprising the plurality of different material layers is introduced between the substrate and the photoimageable material layer.

19. (Canceled)

20. (Previously Presented) The method of claim 1, wherein the dielectric cap layer comprising the plurality of different material layers is introduced between the etch stop layer and the photoimageable material layer.

21-23 (Canceled)

24. (Previously Presented) The method of claim 1, wherein the etch stop layer is silicon nitride.

25. (Canceled)

26. (Previously Presented) The method of claim 1, wherein the plurality of different material layers includes at least one layer of silicon oxynitride.

27. (Canceled)

28. (Previously Presented) A method comprising:
- forming a planarized base layer over a substrate having a plurality of devices;
 - forming a dielectric cap layer over the base layer, wherein the dielectric cap layer is formed by alternating a first material layer and a second material layer a plurality of times, the second material layer formed of a material having a higher dielectric constant than a dielectric constant of a material of the first material layer, wherein collectively the plurality of the first material layer is more than five times thicker than the plurality of second material layer; and
 - patterning an interconnection to a contact point, wherein the dielectric cap layer is configured to suppress substrate reflections during patterning.
29. (Previously Presented) The method of claim 28, wherein the base layer is doped with phosphorous or boron to serve as a collector of metallic contaminants.